

Title (en)

Power semiconductor module for use in power conversion units with downsizing requirements

Title (de)

Halbleitende Baugruppe für Stromrichter-Einheiten mit Verkleinerungsanforderungen

Title (fr)

Module semiconducteur de puissance, utilisé dans des unités de convertisseurs ayant des exigences de miniaturisation

Publication

EP 1121009 A2 20010801 (EN)

Application

EP 01101642 A 20010126

Priority

JP 2000020293 A 20000128

Abstract (en)

A power semiconductor module comprises a circuit board made of an insulating substrate of good thermal conductivity formed with interconnect patterns, a plurality of power semiconductor chips mounted on the circuit board, bonding wires for electrically connecting the semiconductor chips and the interconnect patterns, outer lead terminals fixed to the interconnect patterns, and a resin layer for covering at least the chip mounted surface of the circuit board in its entirety so that the tip of each of the outer lead terminals is exposed. <IMAGE> <IMAGE> <IMAGE>

IPC 1-7

H02M 7/00; H05K 7/14; H01R 13/24

IPC 8 full level

H02M 7/00 (2006.01)

CPC (source: EP US)

H02M 7/003 (2013.01 - EP US); **H01L 2224/48091** (2013.01 - EP US); **H01L 2924/1305** (2013.01 - EP US); **H01L 2924/13055** (2013.01 - EP US); **H01L 2924/13091** (2013.01 - EP US); **H01L 2924/30107** (2013.01 - EP US)

C-Set (source: EP US)

1. **H01L 2224/48091** + **H01L 2924/00014**
2. **H01L 2924/30107** + **H01L 2924/00**
3. **H01L 2924/13091** + **H01L 2924/00**
4. **H01L 2924/13055** + **H01L 2924/00**
5. **H01L 2924/1305** + **H01L 2924/00**

Cited by

EP4258832A1

Designated contracting state (EPC)

DE FR GB

DOCDB simple family (publication)

EP 1121009 A2 20010801; **EP 1121009 A3 20040616**; US 2001015478 A1 20010823; US 6417532 B2 20020709

DOCDB simple family (application)

EP 01101642 A 20010126; US 76939801 A 20010126